

BUK7640-100A

N-channel TrenchMOS standard level FET Rev. 2 — 20 April 2011

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

■ AEC Q101 compliant

Low conduction losses due to low on-state resistance

1.3 Applications

Automotive and general purpose power switching

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I _D	drain current	T _{mb} = 25 °C	-	-	37	Α
P _{tot}	total power dissipation		-	-	138	W
Static cha	racteristics					
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}$	-	30	40	mΩ
Avalanch	Avalanche ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 26 \text{ A; } V_{sup} \leq 25 \text{ V;} \\ R_{GS} &= 50 \Omega; V_{GS} = 10 \text{ V;} \\ T_{j(init)} &= 25 ^{\circ}\text{C; } unclamped \end{split}$	-	-	31	mJ



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		<u>-</u>
2	D	drain[1]	mb	D
3	S	source		
mb	D	mounting base; connected to drain	1 3	mbb076 S
			SOT404 (D2PAK)	

[1] drain (D)

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK7640-100A	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	100	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	T _{mb} = 25 °C	-	37	Α
		T _{mb} = 100 °C	-	26	Α
I _{DM}	peak drain current	T _{mb} = 25 °C; pulsed	-	149	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C	-	138	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drain	diode				
Is	source current	T _{mb} = 25 °C	-	37	Α
I _{SM}	peak source current	pulsed; T _{mb} = 25 °C	-	149	Α
Avalanche rug	gedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 26 A; V_{sup} ≤ 25 V; R_{GS} = 50 Ω ; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	31	mJ

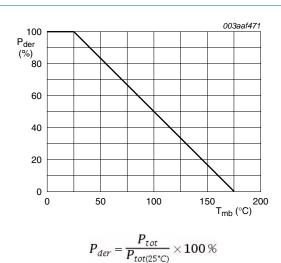
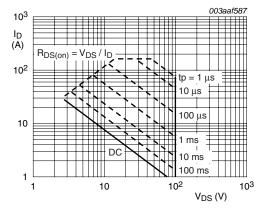
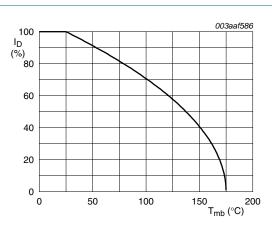


Fig 1. Normalized total power dissipation as a function of mounting base temperature



 T_{mb} = 25 °C; I_{DM} is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



$$I_{\textit{der}} = \frac{I_{\textit{D}}}{I_{\textit{D(25°C)}}} \times 100\,\%$$

V_{GS} ≥ 10 V

Fig 2. Normalized continuous drain current as a function of mounting base temperature

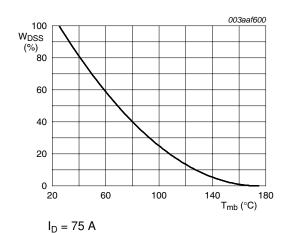
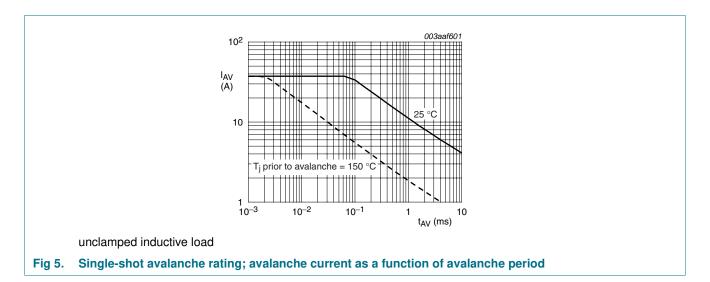


Fig 4. Normalised drain-source non-repetitive avalanche energy as a function of mounting-base temperature

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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base		-	-	1.1	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	minimum footprint; FR4 board	-	50	-	K/W

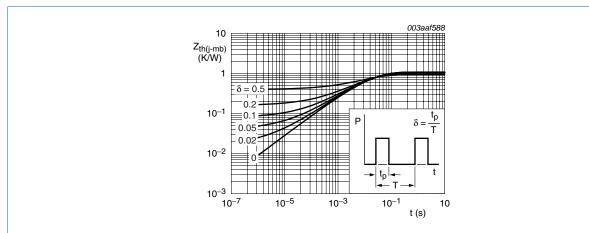


Fig 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	89	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
$V_{GS(th)}$	gate-source threshold	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	2	3	4	V
	voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	4.4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$	1	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C	-	-	108	mΩ
resistance	resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}$	-	30	40	mΩ
Dynamic	characteristics					
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$	-	1720	2293	pF
C _{oss}	output capacitance		-	216	259	pF
C _{rss}	reverse transfer capacitance		-	133	182	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$	-	12	18	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega; T_j = 25 °C$	-	55	83	ns
t _{d(off)}	turn-off delay time		-	48	67	ns
t _f	fall time		-	30	42	ns
L _D	internal drain inductance	measured from upper edge of drain tab to centre of die; $T_j = 25$ °C	-	2.5	-	nΗ
L _S	internal source inductance	measured from source lead soldering point to source bond pad; $T_j = 25 ^{\circ}\text{C}$	-	7.5	-	nΗ
Source-d	rain diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.85	1.2	V
		$I_S = 37 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	1.1	-	V
t _{rr}	reverse recovery time	$I_S = 37 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$;	-	70	-	ns
Qr	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	0.24	-	μC

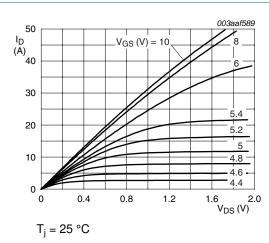


Fig 7. Output characteristics: drain current as a function of drain-source voltage; typical values

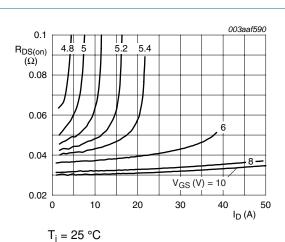


Fig 8. Drain-source on-state resistance as a function of drain current; typical values

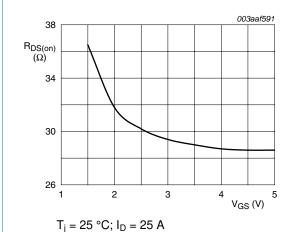


Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

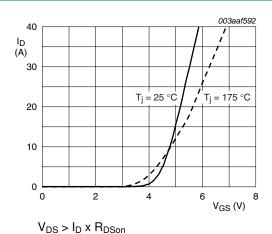


Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

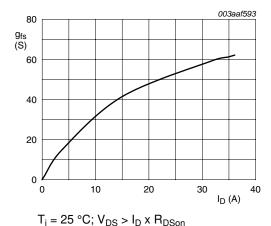
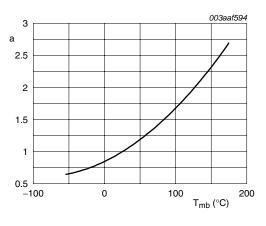


Fig 11. Forward transconductance as a function of drain current; typical values



 $a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$

Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

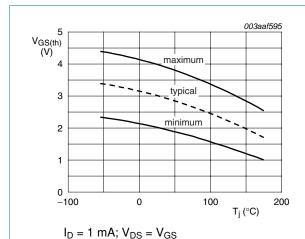
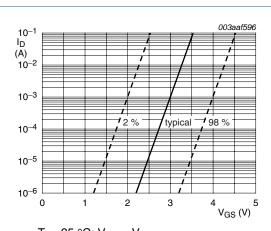


Fig 13. Gate-source threshold voltage as a function of junction temperature



 $T_j = 25 \, ^{\circ}C; \, V_{DS} = V_{GS}$

Fig 14. Sub-threshold drain current as a function of gate-source voltage

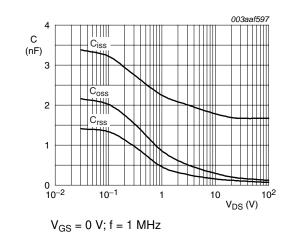


Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

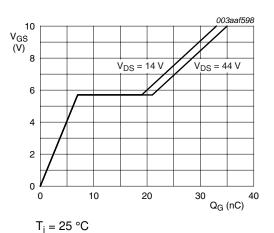
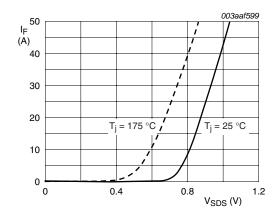


Fig 16. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0 V$

Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

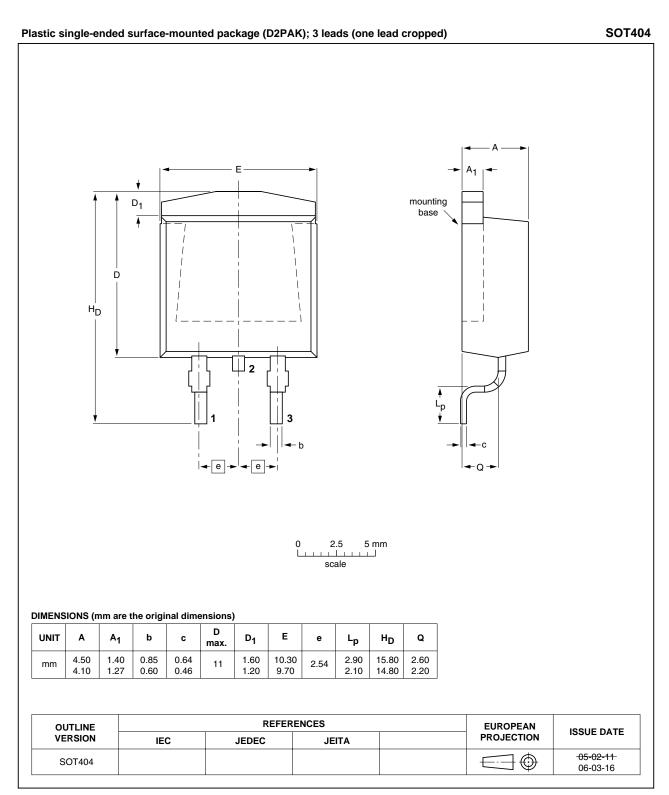


Fig 18. Package outline SOT404 (D2PAK)

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BUK7640-100A v.2	20110420	Product data sheet	-	BUK7640-100A_1		
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity of NXP Semiconductors. 					
 Legal texts have been adapted to the new company name where appropriate. 						
BUK7640-100A_1	19991201	Product specification	-	-		

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9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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